

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE3415 uses advanced trench technology to provide excellent $R_{\rm DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

General Features

• $V_{DS} = -20V, I_D = -4A$

 $R_{DS(ON)}$ < 60m Ω @ V_{GS} =-2.5V

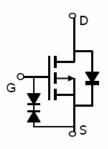
 $R_{DS(ON)}$ < 45m Ω @ V_{GS} =-4.5V

ESD Rating: 2500V HBM

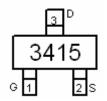
- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM application
- Load switch



Schematic diagram



Marking and pin Assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3415	NCE3415	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit V	
Drain-Source Voltage	V _{DS}	-20		
Gate-Source Voltage	V _G S	±10	V	
Drain Current-Continuous	I _D	-4	Α	
Drain Current-Pulsed (Note 1)	I _{DM}	-30	Α	
Maximum Power Dissipation	P _D	1.4	W	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89.3	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol Condition		Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-20		-	V



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Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-0.35	-0.55	-0.9	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4A	-	34	45	mΩ
Dialii-Source Oil-State Resistance		V _{GS} =-2.5V, I _D =-4A	-	44	60	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-4A	8	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ - 40\/\/ -0\/	-	950	-	PF
Output Capacitance	Coss	V_{DS} =-10V, V_{GS} =0V, F=1.0MHz	-	165	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0IVID2	-	120	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	12		nS
Turn-on Rise Time	t _r	V _{DD} =-10V,R _L =2. 5Ω	_	10		nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-4.5 V , R_{GEN} =3 Ω	-	19		nS
Turn-Off Fall Time	t _f		-	25		nS
Total Gate Charge	Qg	\/ - 40\/ - 40	-	12		nC
Gate-Source Charge	Q _{gs}	V_{DS} =-10V, I_{D} =-4A, V_{GS} =-4.5V	_	1.4	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =-4.5V	-	3.6	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =-4A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-4	Α

Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature}.$
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

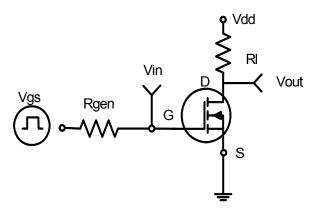


Figure 1:Switching Test Circuit

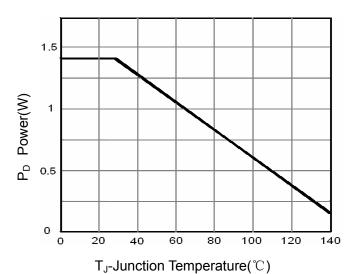


Figure 3 Power Dissipation

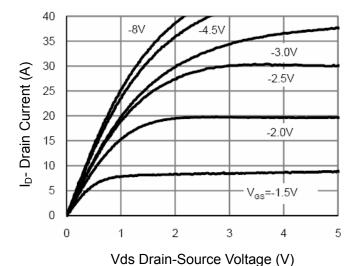


Figure 5 Output Characteristics

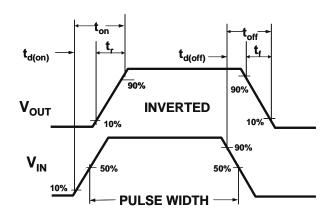


Figure 2:Switching Waveforms

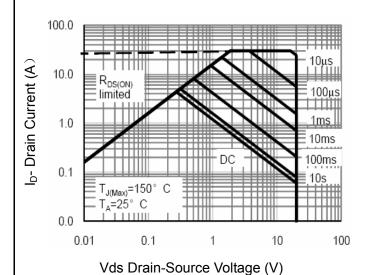


Figure 4 Safe Operation Area

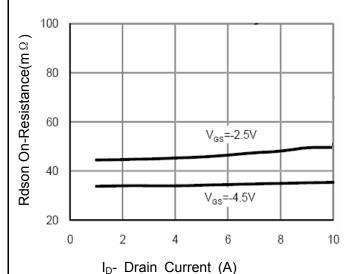
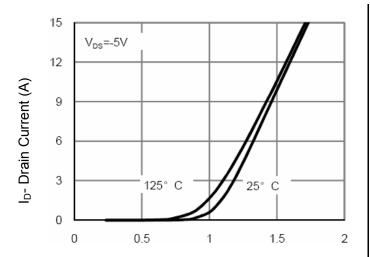


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics

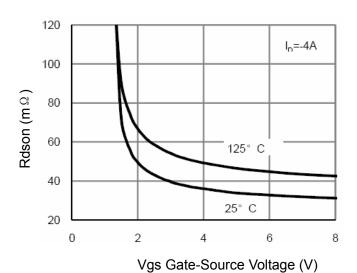


Figure 9 Rdson vs Vgs

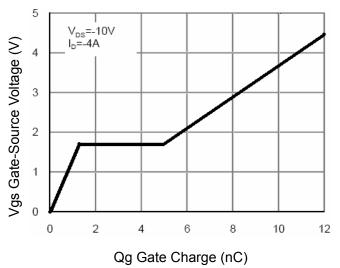


Figure 11 Gate Charge

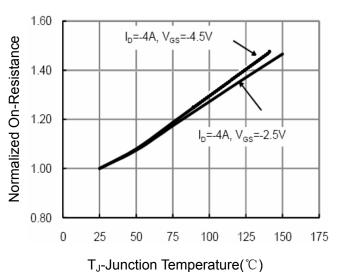


Figure 8 Drain-Source On-Resistance

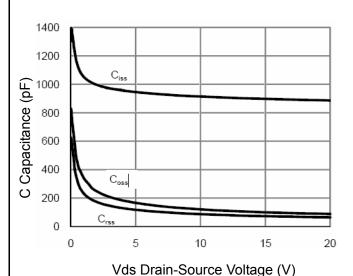


Figure 10 Capacitance vs Vds

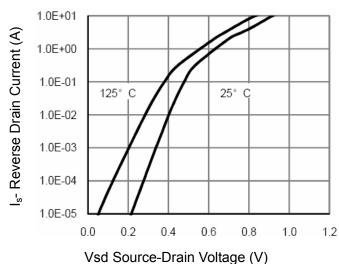
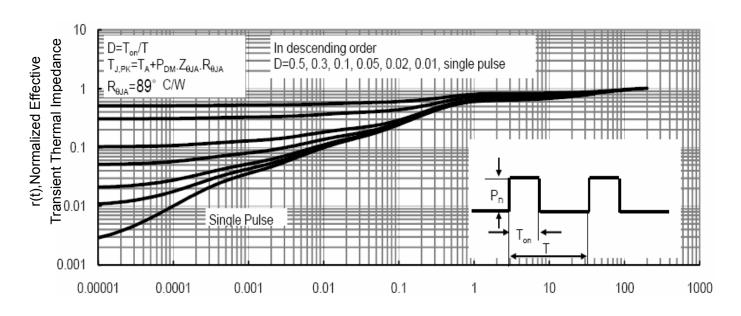


Figure 12 Source- Drain Diode Forward

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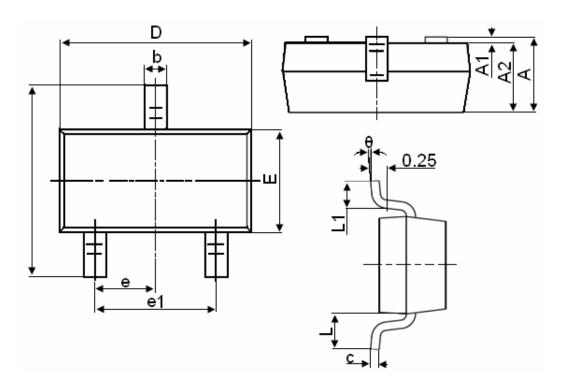


Square Wave Pluse Duration(sec)

Figure 13 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Dimensions in Millimeters				
Symbol	MIN.	MAX.			
Α	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
E	1.200	1.400			
E1	2.250	2.550			
е		0.950TYP			
e1	1.800	2.000			
L	0.550REF				
L1	0.300	0.500			
θ	0°	8°			

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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